

Form 1449*	Atty. Docket No.: 303.324US4	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	Filing Date
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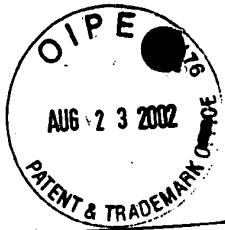
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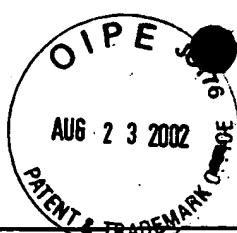
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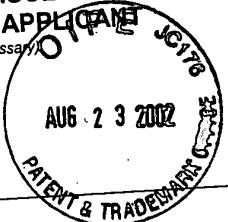
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Application Number	09/691004
Filing Date	October 18, 2000
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Unknown
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